

600V, N-Channel MOSFET

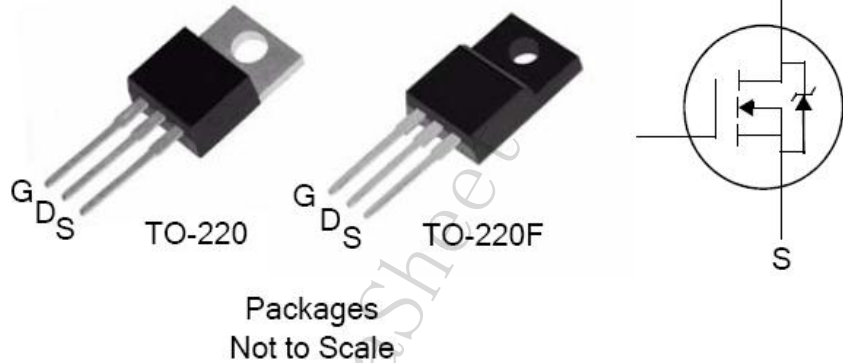
General Features

- Low ON Resistance
- Low Gate Charge
- Peak Current vs. Pulse Width Curve
- RoHS Compliant/Lead Free Package
- Inductive Switching Curves

BV_{DSS}	$R_{DS(ON)}$ (Max.)	I_D
600V	2.2Ω	4.0A

Applications:

- SMPS Power Supply
- Adaptor/Charger
- TV Main Power
- LCD Panel Power



Ordering Codes

Part Number	Package	Marking
FTP04N60	TO-220	FTP04N60
FTA04N60	TO-220F	FTA04N60

Electrical Ratings

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	FTP04N60	FTA04N60	Units
V_{DS}	Drain-to-Source Voltage (NOTE*1)	600		V
I_D	Continuous Drain Current	4.0		A
$I_{D@100^\circ\text{C}}$	Continuous Drain Current	2.5		
I_{DM}	Pulsed Drain Current, $V_{GS}@10\text{V}$ (NOTE*2)	16.0		
P_D	Power Dissipation	86	28	W
	Derating Factor above 25°C	0.69	0.22	W/ $^\circ\text{C}$
V_{GS}	Gate-to-Source Voltage	± 30		V
E_{AS}	Single Pulse Avalanche Energy $L=10\text{mH}$, $I_D=4.0\text{A}$	80		mJ
dv/dt	Peak Diode Recovery dv/dt (NOTE*3)	3.0		V/ns
T_L T_{PKG}	Maximum Temperature for Soldering Leads at 0.063 in (1.6mm) from Case for 10 seconds Package Body for 10 seconds	300 260		$^\circ\text{C}$
T_J and T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150		

*Drain Current limited by Maximum Junction Temperature. Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" Table may cause permanent damage to the device.

Thermal data

Symbol	Parameter	FTP04N60	FTA04N60	Units	Test Conditions
$R_{\theta JC}$	Thermal resistance Junction-to-Case Max	1.45	4.5	°C/W	Water cooled heat sink, P_D adjusted for a peak junction temperature of +150°C
$R_{\theta JA}$	Thermal resistance Junction-to-Ambient Max	62	100		1 cubic foot chamber, free air.

Electrical Characteristics

 OFF Characteristics $T_J=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	600	--	--	V	$V_{GS}=0V, I_D=250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	--	0.6	--	V/°C	Reference to 25°C, $I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	--	--	12	μA	$V_{DS}=600V, V_{GS}=0V$
		--	--	250		$V_{DS}=480V, V_{GS}=0V, T_J=125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	--	--	100	nA	$V_{GS}=+30V$
		--	--	-100		$V_{GS}=-30V$

 ON Characteristics $T_J=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	1.76	2.2	Ω	$V_{GS}=10V, I_D=2.4A$ (NOTE*4)
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	--	4.0	V	$V_{DS} = V_{GS}, I_D=250\mu A$
gfs	Forward Transconductance	--	3.75	--	S	$V_{DS} = 15V, I_D=4A$ (NOTE*4)

Dynamic Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
C_{ISS}	Input Capacitance	--	--	--	pF	$V_{GS}=0V$ $V_{DS}=25V$ $f=1.0MHz$
C_{OSS}	Output Capacitance	--	--	--		
C_{ISS}	Reverse Transfer Capacitance	--	--	--		
Q_G	Total Gate Charge	--	--	--	nC	$V_{DD}=300V$ $I_D=4A$
Q_{GS}	Gate-to-Source Charge	--	--	--		
Q_{GD}	Gate-to-Drain (Miller) Charge	--	--	--		

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	--	--	ns	$V_{DD}=300V$ $I_D=4A$ $V_{GS}=10V$ $R_G=9.1 \Omega$
t_{rise}	Rise Time	--	--	--		
$t_{d(OFF)}$	Turn-off Delay Time	--	--	--		
t_{fall}	Fall Time	--	--	--		

Source-Drian Diode Characteristics $T_J=25^\circ C$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_{SD}	Continuous Source Current(Body Diode)	--	--	4.0	A	Integral pn-diode in MOSFET
I_{SM}	Maximum Pulsed Current(Body Diode)	--	--	16.0	A	
V_{SD}	Diode Forward Voltage	--	--	1.2	V	$I_S=4.0A, V_{GS}=0V$
t_{rr}	Reverse Recovery Time	--	--	--	ns	$V_{GS}=0V$ $I_F=4A, di/dt=100A/us$
Q_{rr}	Reverse Recovery Charge	--	--	--	nC	

NOTE:

- *1. $T_J=+25^\circ C$ to $+150^\circ C$
- *2. Repetitive rating; pulse width limited by maximum junction temperature.
- *3. $I_{SD}=4A$ $di/dt \leq 100A/\mu s$, $V_{DD} \leq BV_{DSS}$, $T_J=+150^\circ C$.
- *4. Pulse width $\leq 380\mu s$; duty cycle $\leq 2\%$.

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